



80V N-Channel Trench Power MOSFET

General Description

The SJ80N070 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 10V. This device is suitable for use as a wide variety of applications.

Features

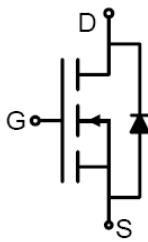
- Low Gate Charge
- 100% UIS Tested, 100% DVDS Tested
- High Power and current handling capability
- Lead free product is acquired

Application

- PWM Applications
- Load Switch
- Power Management

Key Performance Parametes

Parameter	Value	Unit
V_{DS}	80	V
$R_{DS(ON_TYP)}$	7.3	m Ω
I_D	81	A
Q_G	112	nC



Schematic Diagram



TO-220 top view



Package Marking and Ordering Information

Device/Ordering Code	Marking	Package	Packing	Reel Size	Tape width	Quantity
SJ80N070	SJ80N070	TO-220	Tube	\	\	1000 Pcs

Table 1. Absolute Maximum Ratings ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V_{DS}	Drain-Source Voltage ($V_{GS}=0\text{V}$)	80	V
V_{GS}	Gate-Source Voltage ($V_{DS}=0\text{V}$)	± 20	V
I_D	Drain Current-Continuous($T_C=25^{\circ}\text{C}$)	81	A
	Drain Current-Continuous($T_C=100^{\circ}\text{C}$)	51	A
$I_{DM}(\text{pluse})$	Drain Current-Continuous@ Current-Pulsed (Note 1)	324	A
P_D	Maximum Power Dissipation($T_C=25^{\circ}\text{C}$)	125	W
	Maximum Power Dissipation($T_C=100^{\circ}\text{C}$)	50	W
E_{AS}	Avalanche energy (Note 2)	361	mJ
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 150	$^{\circ}\text{C}$

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case		1	$^{\circ}\text{C/W}$



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Table 3. Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V I _D =250μA	80			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =80V, V _{GS} =0V T _J =25℃			1	μA
		V _{DS} =80V, V _{GS} =0V T _J =125℃			100	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	2		4	V
g _{FS}	Forward Transconductance	V _{DS} =10V, I _D =40A		36		S
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =10V, I _D =40A T _J =25℃		7.3	8.7	mΩ
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =40V, V _{GS} =0V, f=1.0MHz		4653		pF
C _{oss}	Output Capacitance			197		pF
C _{rss}	Reverse Transfer Capacitance			171		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1.0MHz		0.65		Ω
Switching Parameters						
t _{d(on)}	Turn-on Delay Time	V _{GS} =10V, V _{DS} =40V, R _L =2Ω, R _{GEN} =6Ω		30		nS
t _r	Turn-on Rise Time			18		nS
t _{d(off)}	Turn-Off Delay Time			65		nS
t _f	Turn-Off Fall Time			30		nS
Q _g	Total Gate Charge	V _{GS} =10V, V _{DS} =40V, I _D =20A		112		nC
Q _{gs}	Gate-Source Charge			15		nC
Q _{gd}	Gate-Drain Charge			45		nC
Source-Drain Diode Characteristics						
I _{SD}	Source-Drain Current (Body Diode)				81	A
V _{SD}	Forward on Voltage ^(Note 3)	V _{GS} =0V, I _S =20A			1.2	V
t _{rr}	Reverse Recovery Time	I _F =20A, dI/dt=100A/μs		39		ns
Q _{rr}	Reverse Recovery Charge	I _F =20A, dI/dt=100A/μs		58		nC

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature.

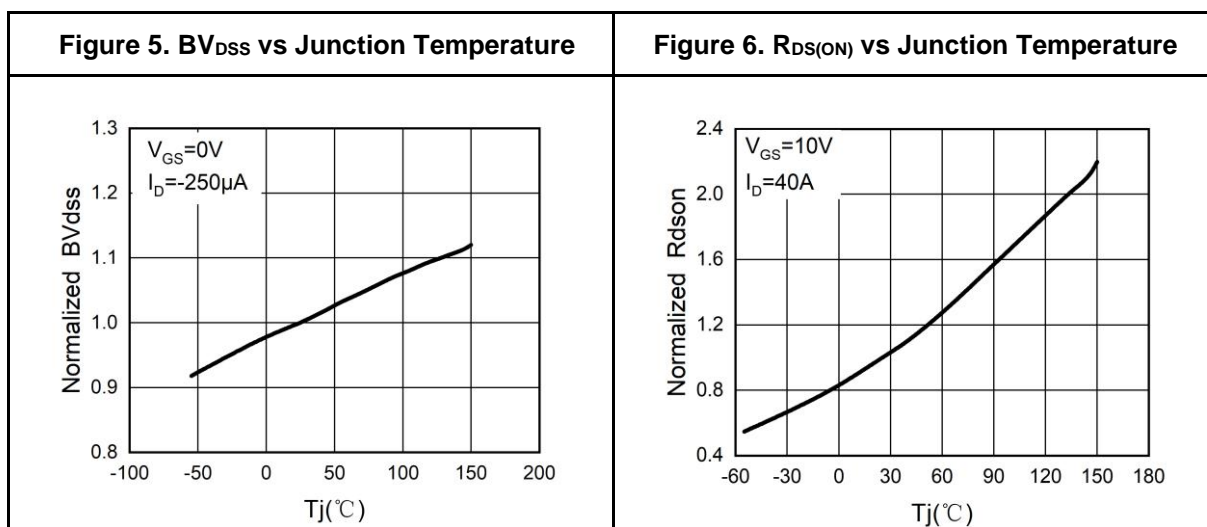
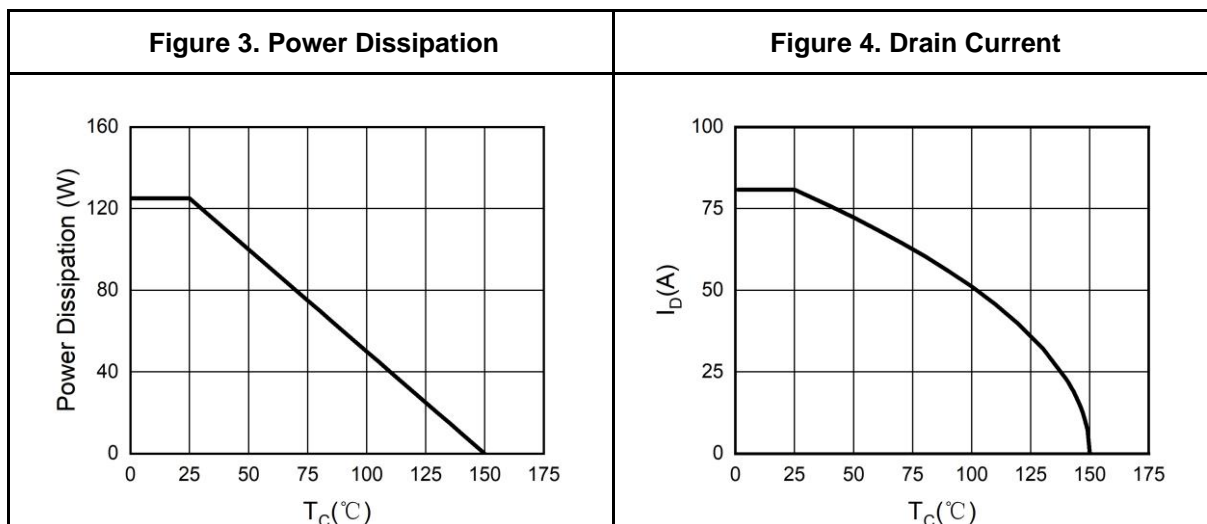
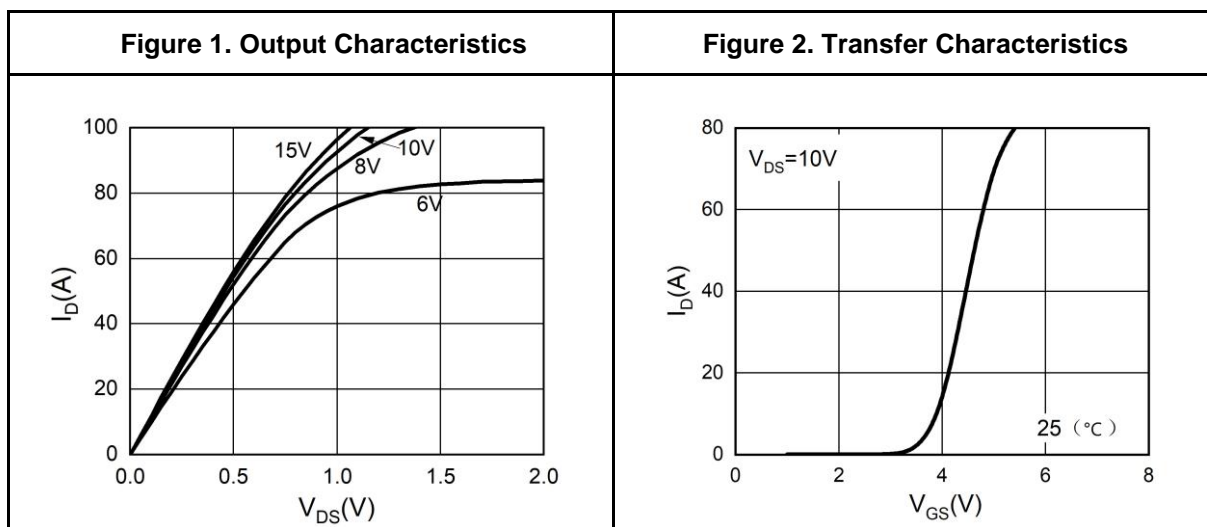
Notes 2.EAS condition: $T_J=25^{\circ}\text{C}, V_{DD}=40V, V_G=10V, R_g=25\Omega, L=0.5\text{mH}$.

Notes 3.Repetitive Rating: Pulse width limited by maximum junction temperature.



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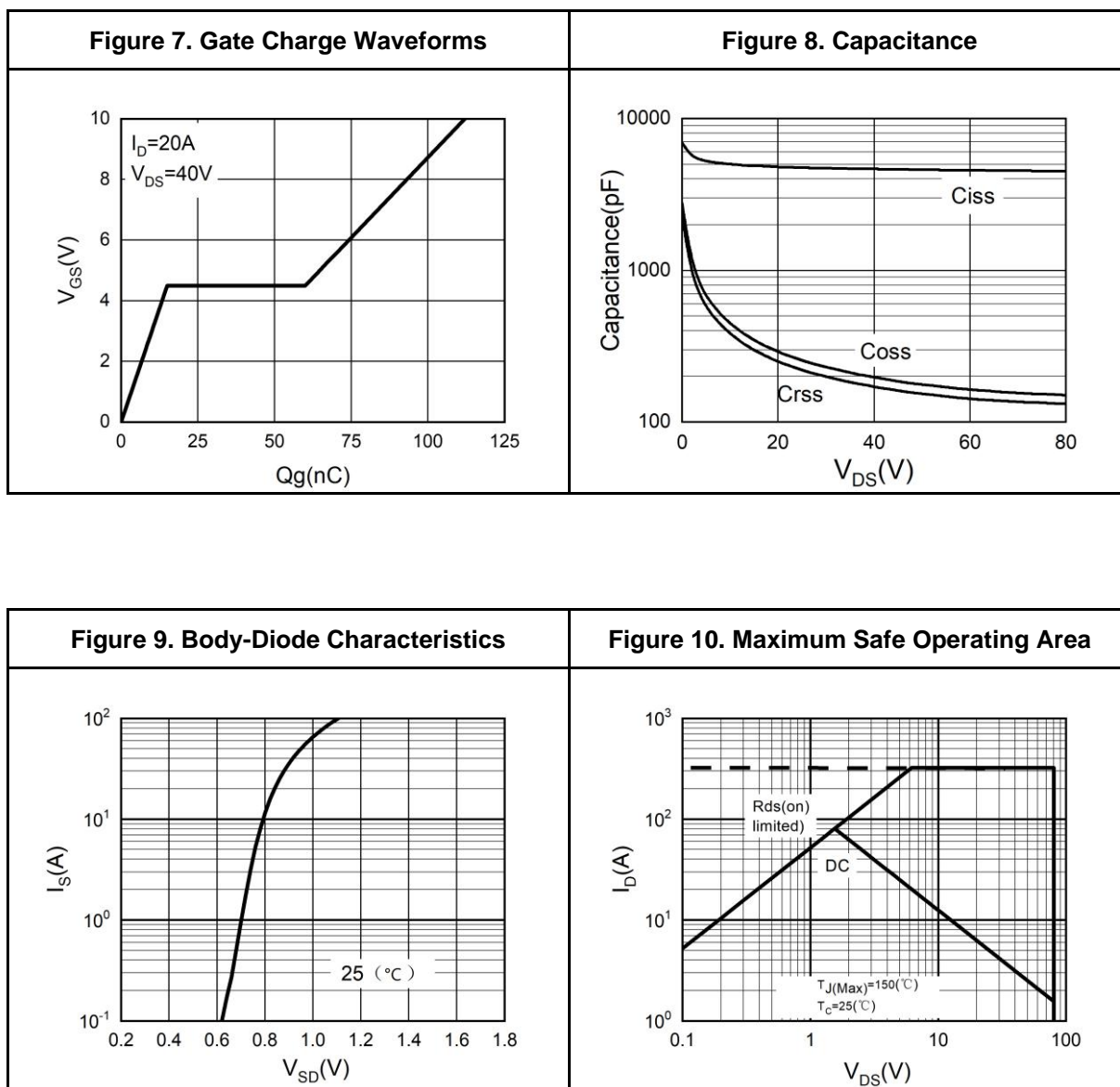
Typical Electrical And Thermal Characteristics (Curves)





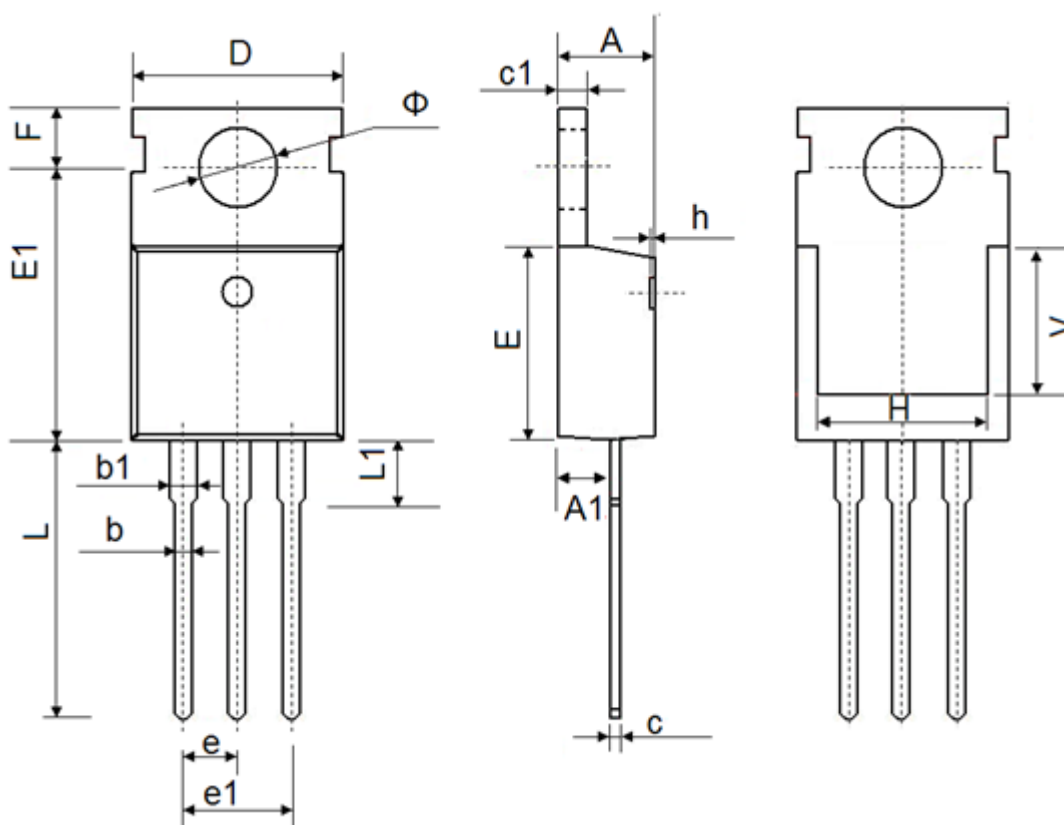
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Typical Electrical And Thermal Characteristics (Curves)





TO-220 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max
A	4.300	4.700	0.169	0.185
A1	2.200	2.600	0.087	0.102
b	0.700	0.950	0.028	0.037
b1	1.170	1.410	0.046	0.056
c	0.450	0.650	0.018	0.026
c1	1.200	1.400	0.047	0.055
D	9.600	10.400	0.378	0.409
E	8.8500	9.750	0.348	0.384
E1	12.650	12.950	0.498	0.510
e	2.540 TYP.		0.100TYP.	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
H	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.750	14.300	0.502	0.563
L1	2.850	3.950	0.112	0.156
V	7.500 REF.		0.295 REF.	
Φ	3.400	4.000	0.134	0.157



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